S/N Unknown PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	303.678US3
Title:	STRUCTURE AND METHOD FOR DUAL GATE OXIDE THICKNESSES		

PRELIMINARY AMENDMENT

BOX PATENT APPLICATION
Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to taking up the above-identified patent application for examination, please amend the application as follows:

IN THE SPECIFICATION

On page 1, line 3, before the heading, "Field of the Invention", insert the following paragraph:

Cross Reference to Related Application(s)

This application is a division of U.S. Patent Application No. 09/514,629, filed on February 28, 2000, the specification of which is incorporated herein by reference.

IN THE CLAIMS

Please cancel claims 1 - 32 and 41 - 54, without prejudice or disclaimer, after adding the following new claims.

55. (New) A logic device and a memory device structure on a single substrate, comprising:

a first transistor, wherein the first transistor includes:

a first dielectric layer of a first thickness less than 5 nanometers (nm);

a top layer which exhibits a high resistance to oxidation at high temperatures; and

a second transistor, wherein the second transistor includes a second dielectric layer of a second thickness.